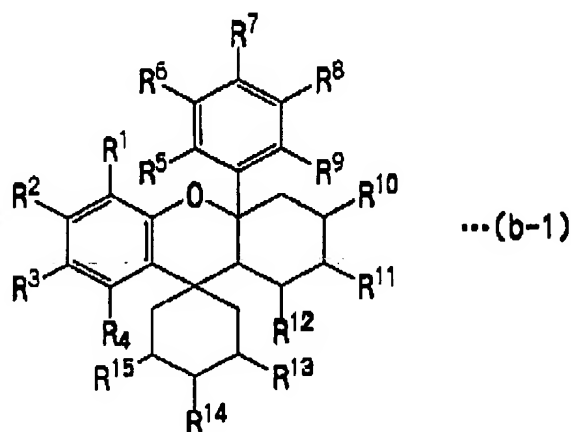


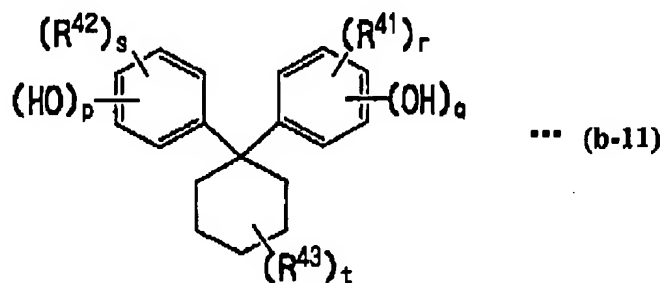
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 Filed : January 12, 2006

AMENDMENTS TO THE CLAIMS

1. (Original) A positive photoresist composition comprising: (A) an alkali-soluble novolak resin in which a portion of hydrogen atoms of all phenolic hydroxyl groups are substituted with 1,2-naphthoquinonediazidesulfonyl groups, and (B) a dissolution promoter comprising at least one compound selected from a group consisting of compounds represented by a general formula (b-1) and a general formula (b-11) shown below:



wherein, R¹ to R⁹ each represent, independently, a hydrogen atom, an alkyl group, a halogen atom, or a hydroxyl group, although at least one of R¹ to R⁹ represents a hydroxyl group; and R¹⁰ to R¹⁵ each represent, independently, a hydrogen atom, an alkyl group, an alkenyl group, a cycloalkyl group or an aryl group;



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wherein, R^{41} to R^{43} each represent, independently, a lower alkyl group, a cycloalkyl group or a lower alkoxy group; p and q each represent an integer from 1 to 3; and r, s and t each represent either 0, or an integer from 1 to 3.

2. **(Original)** A positive photoresist composition according to claim 1, wherein said component (A) is a fractionated resin in which fractionation treatment has been used to reduce a lower molecular weight fraction to no more than 80% by weight of a value prior to said fractionation.

3. **(Original)** A positive photoresist composition according to claim 1, further comprising a photosensitizer (C).

4. **(Original)** A positive photoresist composition according to claim 1, which comprises both (b-1) and (b-11) as dissolution promoters.

5. **(Currently Amended)** A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 4 to a substrate, conducting a prebake, performing selective exposure, and then performing alkali developing to form said resist pattern.